



#9/RCE RCE# 3803 3200

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Request For Continued Examination (RCE) Transmittal Address to: Commissioner for Patents Box RCE Washington, DC 20231	Application Number	10/059,321
	Filing Date	1/31/02
	First Named Inventor	Chuan Lin
	Art Unit	2812
	Examiner Name	I. Stanetta
	Attorney Docket Number	2001 P 14585 US

This is a Request for Continued Examination (RCE) under 37 CFR 1.114 of the above-identified application.
Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.

1. **Submission required under 37 CFR 1.114**

a. ☐ Previously submitted

i. ☐ Consider the amendment(s)/reply under 37 CFR 1.116 previously filed on _____
(Any unentered amendment(s) referred to above will be entered).

ii. ☐ Consider the arguments in the Appeal Brief or Rely Brief previously filed on _____

iii. ☐ Other _____

b. ☒ Enclosed

i. ☐ Amendment/Reply

ii. ☐ Affidavit(s)/ Declaration(s)

iii. ☐ Information Disclosure Statement (IDS)

iv. ☒ Other Preliminary Amendment

2. **Miscellaneous**

a. ☐ Suspension of action on the above-identified application is requested under 37 CFR 1.103(c) for a period of _____ months. (Period of suspension shall not exceed 3 months; Fee under 37 CFR 1.17(i) required)

b. ☐ Other _____

3. **Fees**

The RCE fee under 37 CFR 1.17(e) is required by 37 CFR 1.114 when the RCE is filed.
The Director is hereby authorized to charge the following fees, or credit any overpayments, to

a. ☐ Deposit Account No. _____

i. ☒ RCE fee required under 37 CFR 1.17(e) 02/19/2003 SSESHE1 00000001 10059321

ii. ☒ Extension of time fee (37 CFR 1.136 and 1.17) 01 FC:1801 750.00 OP
02 FC:1251 110.00 OP

iii. ☐ Other _____

b. ☐ Check in the amount of \$ _____ enclosed

c. ☒ Payment by credit card (Form PTO-2038 enclosed)

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

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Name (Print/Type)	Jerome J. Norris	Registration No. (Attorney/Agent)	24,696
Signature	<i>Jerome J. Norris</i>	Date	2/14/03
CERTIFICATE OF MAILING OR TRANSMISSION			
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner For Patents, Box RCE, Washington, DC 20231, or facsimile transmitted to the U.S. Patent and Trademark Office on the date shown below.			
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#10 / Pre-Amended
3/5/03
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: 2001 P 14585 US

In re the application of:)
Chuan Lin) Group Art: 2812
Serial No.: 10/059,321) Examiner: I. Stanetta
Filing Date: January 31, 2002)
Title: REDUCTION OF NEGATIVE BIAS)
TEMPERATURE INSTABILITY IN)
NARROW WIDTH PMOS USING F₂)
IMPLANTATION)

Preliminary Amendment

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In advance of prosecution, and before the application is taken up for examination on the merits, please amend the application as follows:

IN THE CLAIMS:

1. (Twice Amended) In a process of fabricating a narrow channel width PMOSFET device, the improvement of affecting reduction of negative bias temperature instability by use of F₂ side wall implantation [and subsequent high density plasma fill of a STI], comprising:

- a) forming a shallow trench isolation (STI) region in a substrate having a pad oxide and a nitride layer on its surface;
- b) forming a gate on a gate oxide in said substrate;
- c) forming a liner layer in said shallow trench isolation region and subjecting said liner layer to oxidation to form a STI liner oxidation layer;

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